TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

Power dissipation

P_{CM}: 0.8W (Tamb=25℃)

Collector current

I_{CM}: -0.05A

Collector-base voltage

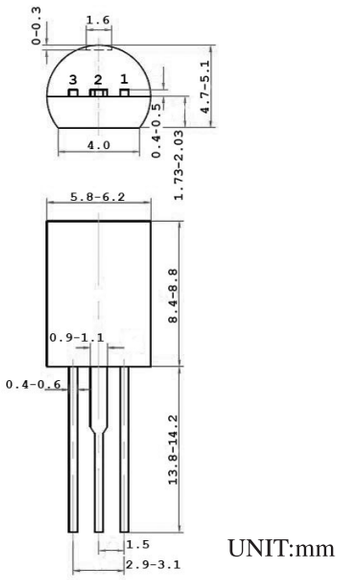
$V_{(BR)CBO}$: -150V

Operating and storage junction temperature range

T_J , T_{stg}: -55℃ to +150℃

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-150		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-5mA, I_B=0	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10 μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-150V, I_E=0		-0.1	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-10mA	40	240	
Collector-emitter saturation voltage	V_{CEsat}	I_C=-10mA, I_B=-1mA		-0.8	V
Transition frequency	f_r	V_{CE}=-30V, I_C=-10mA	80		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240